# **DATA SHEET**



# MOS INTEGRATED CIRCUIT $\mu PD4721$

#### RS-232 LINE DRIVER/RECEIVER AT 3.3 V/5 V

The  $\mu$ PD4721 is a high-breakdown voltage silicon gate CMOS line driver/receiver based on the EIA/TIA-232-E standard. The internal DC/DC converter can switch between multiple voltages, realizing the allowing it to operate with a single +3.3 V or +5 V power supply. It also provides standby function.

This IC incorporates 2 driver circuits and 2 receiver circuits. An RS-232 interface circuit can be easily configured by connecting 5 capacitors externally.

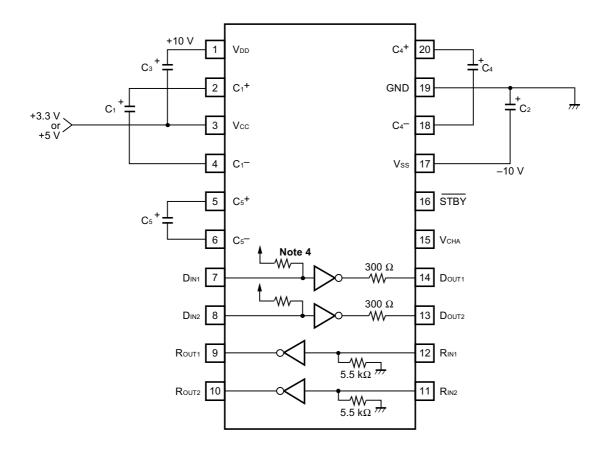
#### **FEATURES**

- · Conforms to EIA/TIA-232-E (former name, RS-232C) standards
- Selectable +3.3 V/+5 V single power supply (selected by VcHA pin)
- By setting the standby pin to a low level (standby mode), circuit current can be reduced. At such times, the driver output is in a high-impedance state.

#### ORDERING INFORMATION

Part number	Package
μPD4721GS-GJG	20-pin plastic SSOP (300 mil)

# **BLOCK DIAGRAM/PIN CONFIGURATION (Top View)**



Note 1. VdD and Vss are output pins stepped up internally. These pins should not be loaded directly.

- 2. Capacitors C<sub>1</sub> to C<sub>5</sub> with a breakdown voltage of 20 V or higher are recommended. And it is recommended to insert the capacitor that is 0.1  $\mu$ F to 1  $\mu$ F between Vcc and GND.
- 3. If VCHA is kept low level (in 5 V mode), capacitor C5 is not necessary.
- 4. The pull-up resistors at driver input are active resistors.



## **Truth Table**

## Driver

STBY	Din	<b>D</b> оит	Remarks
L	×	z	Standby mode (DC/DC converter is stopped)
Н	L	Н	Space level output
Н	Н	L	Mark level output

#### Receiver

STBY	Rin	Rоит	Remarks
L	×	Н	Standby mode (DC/DC converter is stopped)
Н	L	Н	Mark level input
Н	Н	L	Space level input

# 3 V $\leftrightarrow$ 5 V switching $^{\text{Note 5}}$

Vcha	Operating mode					
L 5 V mode (double step-up)						
Н	3 V mode (3 times step-up)					

H: high-level, L: low-level, Z: high-impedance,  $\times$ : H or L

**Note 5**. When switching  $V_{CHA}$ , standby mode must be selected ( $\overline{STBY} = L$ ).



#### **ABSOLUTE MAXIMUM RATINGS** (TA = 25 °C)

Parameter	Symbol	Ratings	Unit
Supply Voltage (VcHA = L)	Vcc	-0.5 to +7.0	٧
Supply Voltage (VcHA = H)	Vcc	-0.5 to +4.5	٧
Driver Input Voltage	Din	−0.5 to Vcc +0.5	V
Receiver Input Voltage	Rin	-30.0 to +30.0	٧
Control Input Voltage (STBY, VcHA)	Vin	-0.5 to Vcc +0.5	٧
Driver Output Voltage	<b>D</b> оит	-25.0 to +25.0 Note 6	V
Receiver Output Voltage	Rоит	-0.5 to Vcc +0.5	V
Input Current (DIN, STBY, VCHA)	lin	±20.0	mA
Operating Ambient Temperature	TA	-40 to +85	°C
Storage Temperature	Tstg	–55 to +150	°C
Total Power Dissipation	Рт	0.5	W

Note 6. Pulse width = 1 ms, duty = 10 % MAX.

#### **RECOMMENDED OPERATING CONDITIONS**

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage (Vcha = L, 5 V mode)	Vcc	4.5	5.0	5.5	V
Supply Voltage (Vcha = H, 3 V mode)	Vcc	3.0	3.3	3.6	V
High-Level Input Voltage (D <sub>IN</sub> )	Vih	2.0		Vcc	V
Low-Level Input Voltage (Din)	VIL	0		0.8	V
High-Level Input Voltage (STBY, VcHA)	Vih	2.4		Vcc	V
Low-Level Input Voltage (STBY, Vcha)	VIL	0		0.6	V
Receiver Input Voltage	Rin	-30		+30	V
Operating Ambient Temperature	TA	-40		+85	°C
Capacitance of External Capacitor	Note 7	0.33		4.7	μF

**Note 7.** In low temperature (below 0 °C), the capacitance of electrolytic capacitor becomes lower. Therefore, set higher values when using in low temperature.

Concerning the wiring length between the capacitor and the IC, the shorter the better.

Capacitors with good frequency characteristics such as tantalum capacitors, laminated ceramic capacitors, and aluminum electrolytic capacitors for switching power supply are recommended for the external capacitors.



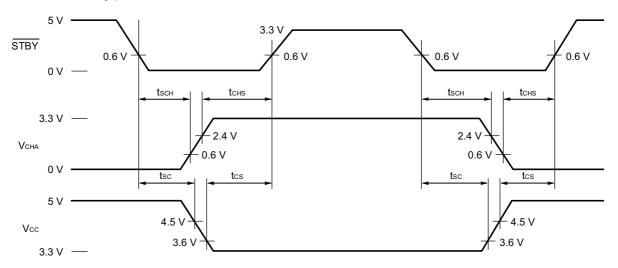
# **ELECTRICAL SPECIFICATIONS (TOTAL)**

(Unless otherwise specified, T<sub>A</sub> = -40 to +85 °C, C<sub>1</sub> to C<sub>5</sub> = 1  $\mu$ F)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current	Icc1	$\frac{\text{Vcc}}{\text{STBY}}$ = H		6.5	13	mA
Girdan Garrenn	1001	$\frac{V_{CC}}{STBY}$ = H		4.5	9	mA
Circuit Current	Icc2	Vcc = +3.3 V, RL = 3 $\underline{\text{k}\Omega}$ (Dout), DIN = GND, RIN, ROUT pin OPEN, $\overline{\text{STBY}}$ = H		19	24	mA
Sireur Guirein	1002	Vcc = +5.0 V,RL = 3 $k\Omega$ (Dout), DiN = GND, RIN, ROUT pin OPEN, $\overline{STBY}$ = H		14	18	mA
		$V_{CC}$ = +3.3 V, No load, D <sub>IN</sub> and R <sub>IN</sub> pins are OPEN, $\overline{STBY}$ = L, T <sub>A</sub> = 25 °C		1	3	μΑ
Circuit Current at Standby	Iccs	$V_{CC}$ = +3.3 V, No load, D <sub>IN</sub> and R <sub>IN</sub> pins are OPEN, $\overline{STBY}$ = L		5		μΑ
Circuit Current at Standby		Vcc = +5.0 V, No load, Din and Rin pins are OPEN, STBY = L, TA = 25 °C		2	5	μΑ
		Vcc = +5.0 V, No load, Din and Rin pins are OPEN, STBY = L		10		μΑ
High-Level Input Voltage	Vін	Vcc = +3.0 to +5.5 V, STBY, Vcha pin	2.4			V
Low-Level Input Voltage	VIL	Vcc = +3.0 to +5.5 V, STBY, Vcна pin			0.6	V
High-Level Input Current	Іін	Vcc = +5.5 V, Vı = +5.5 V, STBY, Vcha pin			1	μΑ
Low-Level Input Current	Iı∟	Vcc = +5.5 V, V <sub>I</sub> = 0 V, STBY, VcHA pin			-1	μΑ
Input Capacitance	Cin	Driver input and receiver input Vcc = +3.3 V, for GND, f = 1 MHz			10	pF
input Gapacitance		Driver input and receiver input Vcc = +5.0 V, for GND, f = 1 MHz			10	pF
STBY — VCHA Time	tscн	$V_{CC}$ = +3.0 to +5.5 V, $\overline{STBY} \downarrow \rightarrow V_{CHA}$ , Note 8	1			μs
V <sub>CHA</sub> — STBY Time	tснs	$V_{CC}$ = +3.0 to +5.5 V, $V_{CHA} \rightarrow \overline{STBY} \uparrow$ , Note 8	1			μs
STBY — Vcc Time	tsc	$Vcc = +3.0 \text{ to } +5.5 \text{ V}, \overline{\text{STBY}} \downarrow \rightarrow Vcc, \text{ Note 8}$	1			μs
Vcc — STBY Time	tcs	$Vcc$ = +3.0 to +5.5 V, $Vcc \rightarrow \overline{STBY} \uparrow$ , Note 8	1			μs

<sup>\*</sup> The TYP. values are for reference at  $T_A$  = 25 °C.

Note 8. Measuring point





# **ELECTRICAL SPECIFICATIONS (DRIVER)**

(Unless otherwise specified, T<sub>A</sub> = -40 to +85 °C, C<sub>1</sub> to C<sub>5</sub> = 1  $\mu$ F)

3 V mode (unless otherwise specified,  $V_{CHA} = H$ ,  $V_{CC} = 3.0$  to 3.6 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Low-Level Input Voltage	VIL				0.8	٧
High-Level Input Voltage	Vін		2.0			V
Low-Level Input Current	I⊫	Vcc = +3.6 V, V <sub>I</sub> = 0 V			-25	μΑ
High-Level Input Current	Іін	Vcc = +3.6 V, Vı = 3.6 V			1.0	μΑ
		Vcc = +3.3 V, R <sub>L</sub> = ∞, T <sub>A</sub> = 25 °C		±9.5		V
Output Voltage	VDO	$V_{CC}$ = +3.3 $V$ , $R_L$ = 3 $k\Omega$ , $T_A$ = $T_{opt}$	±5.0	±6.0		V
		$V_{CC}$ = +3.0 V, $R_L$ = 3 kΩ, $T_A$ = +25 °C	±5.0			V
Output Short-Circuit Current	Isc	Vcc = +3.3 V, for GND			±40	mA
Slew-Rate Note 9	SR	$C_L$ = 10 pF, $R_L$ = 3 to 7 k $\Omega$	3.0		30	V/μs
Siew-Nate	J JK	$C_L$ = 2 500 pF, $R_L$ = 3 to 7 k $\Omega$	3.0		30	V/μs
Propagation Delay Time Note 9	tphl tplh	$R_L = 3 \text{ k}\Omega, C_L = 2 500 \text{ pF}$		2.5		μs
Output Resistor	Ro	$V_{CC} = V_{DD} = V_{SS} = 0 V$ $V_{OUT} = \pm 2 V$	300			Ω
Standby Output Transfer Time	tdaz	$R_L = 3 \text{ k}\Omega, C_L = 2 500 \text{ pF}, \text{Note } 10$		4	10	μs
Standby Output Transfer Time	tdza	$R_L = 3 \text{ k}\Omega$ , $C_L = 2 500 \text{ pF}$ , Note 10		1	3	ms
Power-On Output Transfer Time	tpra	$R_L = 3 \text{ k}\Omega, C_L = 2 500 \text{ pF}, \text{Note 11}$		1	3	ms

<sup>\*</sup> The TYP. values are for reference at  $T_A$  = 25 °C.

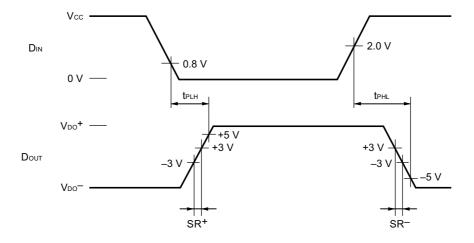


5 V mode (Unless otherwise specified, Vcha = L, Vcc = +5.0 V  $\pm$  10 %)

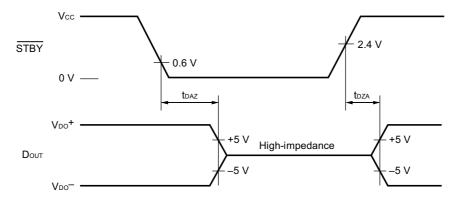
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Low-Level Input Voltage	VIL				0.8	٧
High-Level Input Voltage	Vін		2.0			V
Low-Level Input Current	I⊫	Vcc = +5.5 V, V <sub>I</sub> = 0 V			-40	μΑ
High-Level Input Current	Іін	Vcc = +5.5 V, Vı = 5.5 V			1.0	μΑ
		Vcc = +5.0 V, R <sub>L</sub> = ∞, T <sub>A</sub> = 25 °C		±9.7		V
Output Voltage	VDO	$V_{CC}$ = +5.0 V, $R_L$ = 3 k $\Omega$ , $T_A$ = $T_{opt}$	±6.0			V
		$V_{CC}$ = +4.5 V, $R_L$ = 3 k $\Omega$ , $T_A$ = $T_{opt}$	±5.0			V
Output Short-Circuit Current	Isc	Vcc = +5.0 V, for GND			±40	mA
		$C_L$ = 10 pF, $R_L$ = 3 to 7 k $\Omega$	4.0		30	V/μs
Slew-Rate Note 9	SR	$C_L$ = 2 500 pF, $R_L$ = 3 to 7 k $\Omega$	4.0		30	V/μs
Propagation Delay Time Note 9	tрнг tргн	$R_L = 3 \text{ k}\Omega, C_L = 2 500 \text{ pF}$		2		μs
Output Resistor	Ro	$V_{CC} = V_{DD} = V_{SS} = 0 V$ $V_{OUT} = \pm 2 V$	300			Ω
Standby Output Transfer Time	tdaz	$R_L = 3 \text{ k}\Omega$ , $C_L = 2 500 \text{ pF}$ , Note 10		4	10	μs
Standby Output Transfer Time	tdza	$R_L = 3 \text{ k}\Omega$ , $C_L = 2 500 \text{ pF}$ , Note 10		0.5	1	ms
Power-On Output Transfer Time	tpra	$R_L = 3 \text{ k}\Omega$ , $C_L = 2 500 \text{ pF}$ , Note 12		0.5	1	ms

<sup>\*</sup> The TYP. values are for reference at  $T_A$  = 25 °C.

Note 9. Measuring point

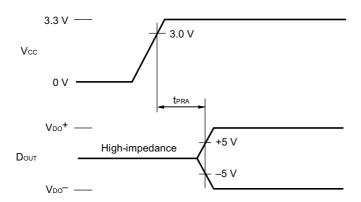


Note 10. Measuring point



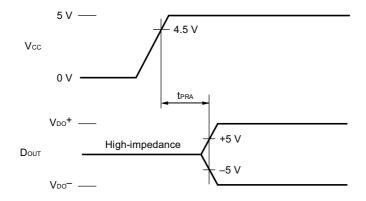
Driver outputs are indefinite during transition time (tdzA).

Note 11. Measuring point



Driver outputs are indefinite during transition time (tpra).

Note 12. Measuring point



Driver outputs are indefinite during transition time (tpra).



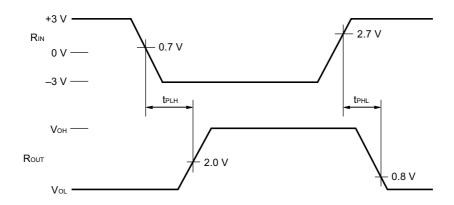
# **ELECTRICAL SPECIFICATIONS (RECEIVER)**

(Unless otherwise specified, Vcc = 3.0 to 5.5 V, TA = -40 to +85 °C, C1 to C5 = 1  $\mu$ F)

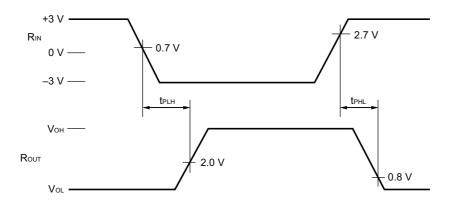
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Low-Level Output Voltage	V <sub>OL1</sub>	Iουτ = 4 mA, STBY = H			0.4	V
High-Level Output Voltage	V <sub>OH1</sub>	Iουτ = -4 mA, STBY = H	Vcc – 0.4			V
Low-Level Output Voltage	V <sub>OL2</sub>	IOUT = 4 mA, STBY = L			0.5	V
High-Level Output Voltage	V <sub>OH2</sub>	Iouτ = -4 mA, STBY = L	Vcc – 0.5			V
Propagation Delay Time (STBY = H)	t <sub>PHL</sub>	$R_{IN} \rightarrow R_{OUT}, C_L = 150 pF$ $V_{CC} = +3.0 V, Note 13$		0.2		μs
Input Resistor	Rı		3	5.5	7	kΩ
Input Pin Open Voltage	Vio				0.5	V
	Vін	Vcc = +3.0 to +5.5 V	1.7	2.3	2.7	V
Input Threshold (STBY = H)	VIL	Vcc = +3.0 to +5.5 V	0.7	1.1	1.7	V
	Vн	Vcc = +3.0 to +5.5 V (Hysteresis width)	0.5	1.2	1.8	V
Standby Output Transfer Time	<b>t</b> DAH	Note 15		0.2	3	μs
Standby Output Transfer Time	<b>+</b>	V <sub>CHA</sub> = H (3 V mode) Note 15		0.6	3	ms
Standby Output Transfer Time	t <sub>DHA</sub>	V <sub>CHA</sub> = L (5 V mode) Note 15		0.3	1	ms
Power-On Reset Release Time	+	V <sub>CHA</sub> = H (3 V mode) Note 16		1	3	ms
rower-on Reset Release Time	tpra	V <sub>CHA</sub> = L (5 V mode) Note 17		0.5	1	ms

<sup>\*</sup> The TYP. values are for reference at T<sub>A</sub> = 25  $^{\circ}$ C.

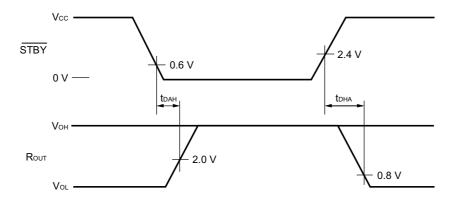
Note 13. Measuring point



Note 14. Measuring point

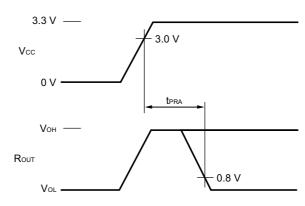


Note 15. Measuring point



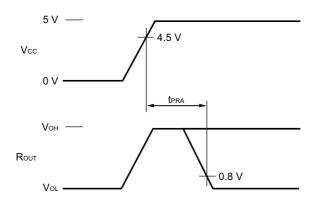
Receiver outputs are indefinite during transition time (tdha).

Note 16. Measuring point



Receiver outputs are indefinite during reset release time (tpra).

Note 17. Measuring point



Receiver outputs are indefinite during reset release time (tpra).

## REFERENCE MATERIAL

- IC PACKAGE MANUAL (C10943X)
- NEC SEMICONDUCTOR DEVICE RELIABILITY/QUALITY (IEI-1212)



## **RECOMMENDED SOLDERING CONDITIONS**

The following conditions (See table below) must be met when soldering this product.

Please consult with our sales offices in case other soldering process is used, or in case soldering is done under different conditions.

## TYPES OF SURFACE MOUNT DEVICE

For more details, refer to our document "SMT MANUAL" (C10535E).

## $\mu$ PD4721 GS-GJG

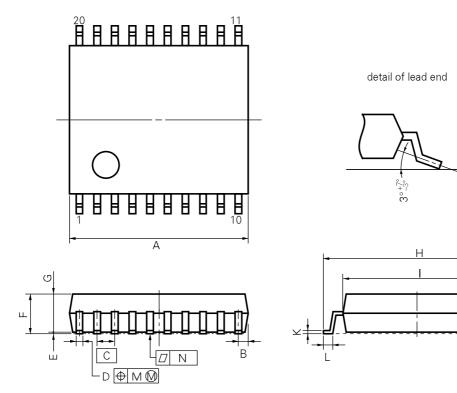
Soldering process	Soldering conditions	Symbol
Infrared ray reflow	Peak package's surface temperature: 230 °C or below, Reflow time: 30 seconds or below (210 °C or higher), Number of reflow process: 2, Exposure limit*: None	IR30-00-2
VPS	Peak package's surface temperature: 215 °C or below, Reflow time: 40 seconds or below (200 °C or higher), Number of reflow process: 2, Exposure limit*: None	VP15-00-2
Wave soldering	Solder Temperature: 260 °C or lower, Reflow time: Within 10 sec, Number of reflowprocess: 1, Exposure limit*: None	WS60-00-1
Partial heating method	Terminal temperature: 300 °C or below, Flow time: 10 seconds or below, Exposure limit*: None	0

<sup>\*</sup> Exposure limit before soldering after dry-pack package is opened. Storage conditions: 25 °C and relative humidity at 65 % or less.

Note Do not apply more than a single process at once, except for "Partial heating method"

# **PACKAGE DRAWINGS**

# 20 PIN PLASTIC SHRINK SOP (300 mil)



## NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

P20GM-65-300B-2

ITEM	MILLIMETERS	INCHES
А	7.00 MAX.	0.276 MAX.
В	0.575 MAX.	0.023 MAX.
С	0.65 (T.P.)	0.026 (T.P.)
D	0.30±0.10	0.012+0.004
Е	0.125±0.075	0.005±0.003
F	2.0 MAX.	0.079 MAX.
G	1.7	0.067
Н	8.1±0.3	0.319±0.012
I	6.1±0.2	0.240±0.008
J	1.0±0.2	0.039+0.009
K	0.15+0.10	0.006+0.004
L	0.5±0.2	0.020+0.008
М	0.12	0.005
N	0.10	0.004

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Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

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